

# TF2117/TF2118

# Single Channel Driver

#### **Features**

- Floating channel in bootstrap operation to 600V
- Drives one N-channel MOSFET or IGBT
- Outputs tolerant to negative transients
- Wide logic supply: 10V to 20V
- Schmitt triggered logic input with internal pull down
- Undervoltage lockout for V<sub>cc</sub> and V<sub>RS</sub>
- Extended temperature range: -40°C to +125°C

# **Applications**

- DC-DC Converters
- AC-DC Inverters
- Motor Controls
- Class D Power Amplifiers

# **Description**

The TF2117 and TF2118 are high voltage, high speed gate drivers capable of driving one N-channel MOSFETs and IGBTs in a bootstrap operation. TF Semiconductor's high voltage process enables the TF2117 and TF2118 to switch at 600V. The TF2117 and TF2118 logic input is compatible with standard CMOS outputs (to 3.3V). The driver output features high pulse current buffers designed for minimum driver cross conduction. The single floating channel can be used in high side or low side configuration.

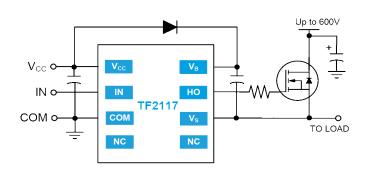
The TF2117 and TF2118 are offered in a space saving 8-pin SOIC and 8-pin PDIP package. They operate over an extended -40 °C to +125 °C temperature range.

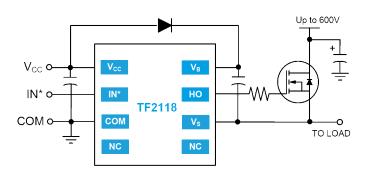




PDIP-8

# **Typical Application**





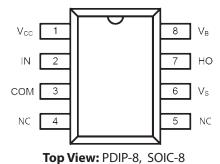
## **Ordering Information**

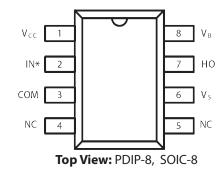
Year Year Week Week

		Y	ear Year VVeek VVeek
<b>PART NUMBER</b>	PACKAGE	PACK / Qty	MARK
TF2117-TAU	5015.0	Tube / 100	YYWW
TF2117-TAH	SOIC-8	T&R / 2500	TF2117 Lot ID
TF2117-3AS	PDIP-8	Tube / 50	TF2117 Lot ID
TF2118-TAU		Tube / 100	YYWW
TF2118-TAH	SOIC-8	T&R / 2500	TF2118 Lot ID
TF2118-3AS	PDIP-8	Tube / 50	TF2118 Lot ID

www.tfsemi.com Rev. 2.2







TF2118

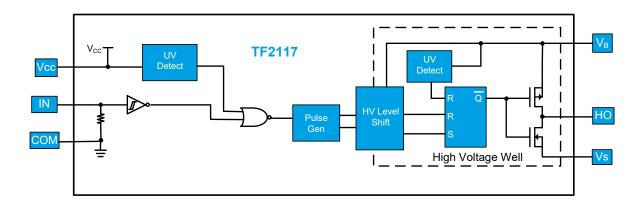
#### TF2117

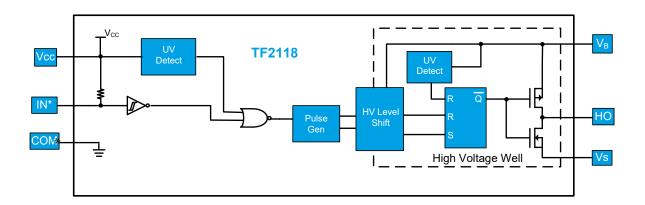
# **Pin Descriptions**

PIN NAME	PIN DESCRIPTION
VCC	Logic and gate drive supply
IN	TF2117 Logic input for gate driver output (HO), in phase with HO
IN*	TF2118 Logic input for gate driver output (HO), out of phase with HO
COM	Logic ground
NC	No Connect
V <sub>s</sub>	High-side floating supply return
НО	High-side gate drive output
V <sub>B</sub>	High-side floating supply



# **Functional Block Diagram**







# Absolute Maximum Ratings (NOTE1)

$V_B$ - High side floating supply voltage0.3V to +624V
$V_s$ - High side floating supply offset voltage $V_B$ -24V to $V_B$ +0.3V
$V_{HO}$ - High side floating output voltage $V_s$ -0.3V to $V_B$ +0.3V
V <sub>cc</sub> - Logic supply voltage0.3V to +24V
$V_{IN}^{-}$ - Logic input voltage0.3V to $V_{CC}^{-}$ +0.3V
$dV_s$ / dt - Allowable offset supply voltage transient50 V/ns
$P_D$ - Package power dissipation at $T_A \le 25$ °C
SOIC-80.625W
PDIP-81.0W
R <sub>OJA</sub> - Thermal Resistance, junction to Ambient
SOIC-8200°C/W
DDID 8 200°C /W

**NOTE1** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

T <sub>1</sub> - Junction temperature	+150 °C
T <sub>s</sub> - Storage temerature	55 to 150 °C
T <sub>L</sub> - Lead Temperature (soldering, 10 seconds	300 °C
SOIC-8 Thermal Resistance (NOTE2)	
$\theta_{IC}$	45 °C/W
θ,μ	200 °C/W
PDIP-8 Thermal Resistance (NOTE2)	
$\theta_{IC}$	35 °C/W
$\theta_{IA}$	125 °C/W
<del></del>	

**NOTE2** When mounted on a standard JEDEC 2-layer FR-4 board.

# **Recommended Operating Conditions**

Symbol	Parameter	MIN	ТҮР	MAX	Unit
V <sub>B</sub>	High side floating supply absolute voltage	V <sub>s</sub> + 10		V <sub>s</sub> + 20	
V <sub>s</sub>	High side floating supply offset voltage	NOTE3		600	
V <sub>HO</sub>	High side floating output voltage	V <sub>s</sub>		V <sub>B</sub>	V
V <sub>cc</sub>	Low side and logic fixed supply voltage	10		20	V
V <sub>IN</sub>	Logic input voltage (IN/IN*)	0		V <sub>cc</sub>	
T <sub>A</sub>	Ambient temperature	-40		125	°C

**NOTE3** Logic operational for VS of -5V to +600V.



#### **DC Electrical Characteristics** (NOTE4)

 $\rm V_{BIAS}(\rm V_{CC}, \rm V_{BS}\,) = 15V, \rm T_A = 25~^{\circ}C$  , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit	
V <sub>IH</sub>	Logic "1" input voltage		9.5				
V <sub>IL</sub>	Logic "0" input voltage	NOTE 5			6.0	V	
V <sub>OH</sub>	High level output voltage, V <sub>BIAS</sub> - V <sub>O</sub>	I <sub>O</sub> = 2mA		0.05	0.2		
V <sub>OL</sub>	Low level output voltage, V <sub>o</sub>	$I_0 = 2mA$		0.02	0.1	]	
I <sub>LK</sub>	Offset supply leakage current	VB = VS = 600V			50		
I <sub>BSQ</sub>	Quiescent V <sub>BS</sub> supply current	$V_{IN} = 0V \text{ or } V_{CC}$		50	240	]	
I <sub>CCQ</sub>	Quiescent V <sub>CC</sub> supply current	$V_{IN} = 0V \text{ or } V_{CC}$		70	340	μΑ	
I <sub>IN+</sub>	Logic "1" input bias current	$V_{IN} = V_{CC}$		20	40	]	
I <sub>IN-</sub>	Logic "0" input bias current	V <sub>IN</sub> = 0V			5.0		
$V_{BSUV+}$	V <sub>BS</sub> supply under-voltage positive going threshold		7.6	8.6	9.6		
V <sub>BSUV</sub> -	V <sub>BS</sub> supply under-voltage negative going threshold		7.2	8.2	9.2	V	
$V_{CCUV+}$	V <sub>cc</sub> supply under-voltage positive going threshold		7.6	8.6	9.6	V	
V <sub>CCUV</sub> -	V <sub>cc</sub> supply under-voltage negative going threshold		7.2	8.2	9.2	-	
I <sub>O+</sub>	Output high short circuit pulsed current	$V_0 = 0V, V_{IN} = Logic "1",$ PW \le 10 \mus	200	290		mA	
I <sub>O-</sub>	Output low short circuit pulsed current	$V_0 = 15V$ , $V_{IN} = Logic "0"$ , PW $\leq 10 \mu s$	420	600			

**NOTE4** The  $V_{NV}$   $V_{THY}$  and  $I_{NV}$  parameters are referenced to COM and are applicable to logic input pins: IN and IN\*. The  $V_0$  and  $I_0$  parameters are referenced to COM and are applicable to the output pins HO.

**NOTE5** For optimal operation, it is recommended that the input pulse (to IN and IN\*) should have an amplitude of 9.5V minimum with a pulse width of 250ns minimum.

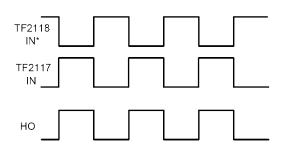


#### **AC Electrical Characteristics**

 $V_{BIAS}(V_{CC},V_{BS})=15V,C_{L}=1000pF,\ and\ T_{A}=25\ ^{\circ}C,\ unless \ otherwise\ specified.$ 

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t <sub>on</sub>	Turn-on propagation delay	$V_S = 0V$		125	200	
t <sub>OFF</sub>	Turn-off propagation delay	V <sub>s</sub> = 600V		105	180	ns
t <sub>r</sub>	Turn-on rise time			75	130	
t <sub>f</sub>	Turn-off fall time			35	65	

# **Timing Waveforms**



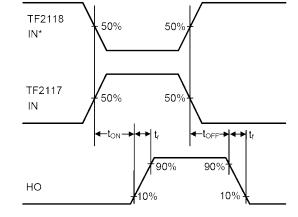


Figure 1. Input / Output Timing Diagram

Figure 2. Switching Time Waveform Definitions

# **Application Information**

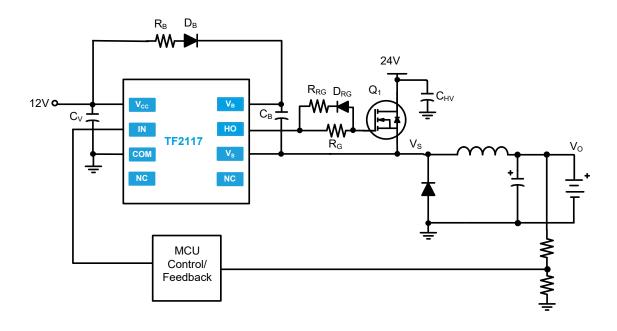


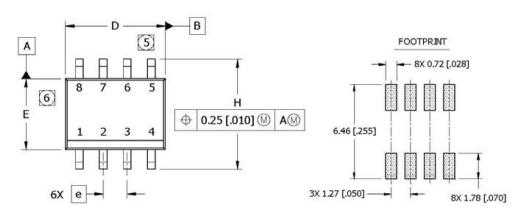
Figure 3. Buck converter using TF2117 in basic battery charger application

- RRG value is typically between  $5\Omega$  and  $10\Omega$ , exact value decided by MOSFET junction capacitance and drive current of gate driver;  $10\Omega$  is used in this example.
- RG value is typically between  $10\Omega$  and  $50\Omega$ , exact value decided by MOSFET junction capacitance and drive current of gate driver;  $20\Omega$  is used in this example.
- RB value is typically between  $3\Omega$  and  $20\Omega$ , exact value depending on bootstrap capacitor value and amount of current limiting required for bootstrap capacitor charging;  $10\Omega$  is used in this example. Also DB should be an ultra fast diode of 1A rating minimum and voltage rating greater than system operating voltage.
- It is recommended that the input pulse (to IN) should have an amplitude of 9.5V minimum (for VDD=15V) with a minimum pulse width of 250ns.

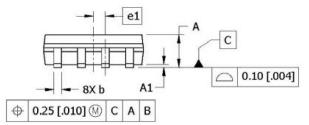


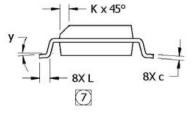
# **Package Dimensions (SOIC-8 N)**

Please contact support@tfsemi.com for package availability.



DIM	INCHES		MILLIN	1ETERS
DIM	MIN	MAX	MIN	MAX
Α	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
С	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
е	.050 BASIC		1.27 BASIC	
e 1	.025 B	ASIC	0.635	BASIC
Н	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
У	00	80	00	80





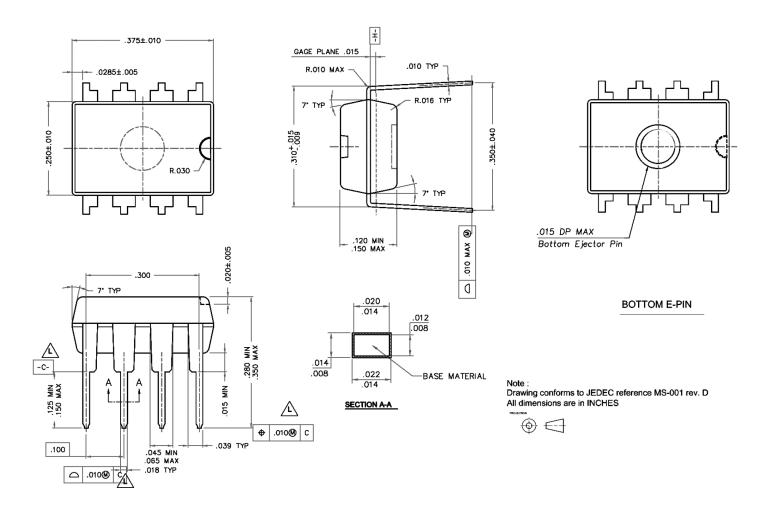
#### NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- (5) DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
- 6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
- DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

01-6027

# **Package Dimensions (PDIP-8)**

Please contact support@tfsemi.com for package availability.





Rev.	Change	Owner	Date
2.0	First release, Advance info datasheet	Keith Spaulding	12/5/2015
2.1	Add note 5	Keith Spaulding	10/31/2019
2.2	Add Application Information, pg. 7	Keith Spaulding	5/18/2020

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